

2SK3634-VB Datasheet N-Channel 200 V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}$ (Ω)	I _D (A)			
200	0.270 at V _{GS} = 10 V	8			

FEATURES

- Trench Power MOSFET
- 175 °C Junction Temperature
- PWM Optimized
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC





G D S

Top View

TO-251



N-Channel MOSFET

APPLICATIONS

· Primary Side Switch

ABSOLUTE MAXIMUM RATINGS (TA	= 25 °C, unless othe	rwise noted)			
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	200	\/	
Gate-Source Voltage		V _{GS}	± 20	V	
Continuous Dunis Comment /T 475 90\b	T _C = 25 °C	I-	8		
Continuous Drain Current (T _J = 175 °C) ^b	T _C = 125 °C	- I _D	5		
Pulsed Drain Current		I _{DM}	25	А	
Continuous Source Current (Diode Conduction)		I _S	5		
Avalanche Current		I _{AS}	5		
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	18	mJ	
Mayimum Dayor Dissination	T _C = 25 °C	P _D	96 ^b	W	
Maximum Power Dissipation	T _A = 25 °C	'D	3 ^a		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
lunation to Ambiant	t ≤ 10 s	R _{thJA}	15	18	°C/W	
Junction-to-Ambient ^a	Steady State		40	50		
Junction-to-Case (Drain)	•	R _{thJC}	0.85	1.1		

Notes:

- a. Surface mounted on 1" x 1" FR4 board.
- b. See SOA curve for voltage derating.

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Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	200			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2		4	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V _{DS} = 200 V, V _{GS} = 0 V			1		
Zero Gate Voltage Drain Current	I_{DSS}	V _{DS} = 200 V, V _{GS} = 0 V, T _J = 125 °C			50	'	
		V _{DS} = 200 V, V _{GS} = 0 V, T _J = 175 °C			250		
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	40			Α	
		$V_{GS} = 10 \text{ V}, I_D = 3 \text{ A}$		0.270			
Danie Course On Chata Besistance	R	V _{GS} = 10 V, I _D = 3 A, T _J = 125 °C		0.300		Ω	
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 3 A, T _J = 175 °C		0.320			
		V _{GS} = 6 V, I _D = 3 A		0.310		1	
Forward Transconductance ^b	9 _{fs}	V _{DS} = 15 V, I _D = 3 A		35		S	
Dynamic ^a							
Input Capacitance	C_{iss}			800		pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, F = 1 \text{ MHz}$		100			
Reverse Transfer Capacitance	C _{rss}			50			
Total Gate Charge ^c	Q_g			34	51		
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 100 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 3 \text{ A}$		8		nC	
Gate-Drain Charge ^c	Q_{gd}			12			
Gate Resistance	R_g		0.5		2.9	Ω	
Turn-On Delay Time ^c	t _{d(on)}			15	25		
Rise Time ^c	t _r	$V_{DD} = 100 \text{ V}, R_{L} = 5.2 \Omega$		50	75	ns	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 3 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 2.5 \Omega$		30	45		
Fall Time ^c	t _f			60	90		
Source-Drain Diode Ratings and Char	acteristics (7	T _C = 25 °C)					
Pulsed Current	I _{SM}				5	Α	
Diode Forward Voltage ^b	V _{SD}	I _F = 3 A, V _{GS} = 0 V		0.9	1.5	V	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 3 A, dI/dt = 100 A/μs		180	250	ns	

Notes:

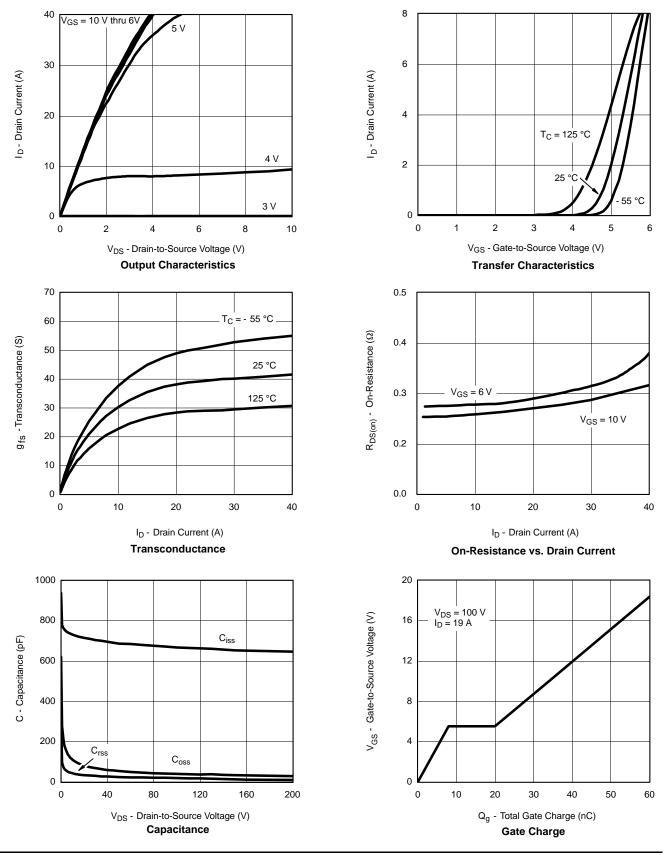
- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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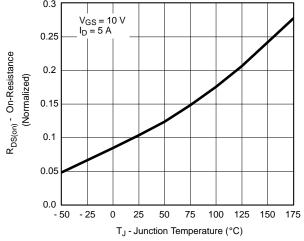
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



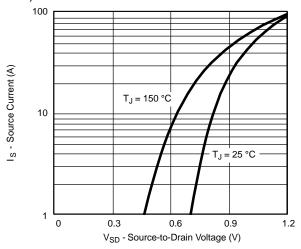
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



On-Resistance vs. Junction Temperature

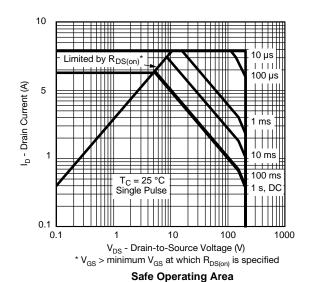


Source-Drain Diode Forward Voltage

THERMAL RATINGS



Maximum Avalanche Drain Current vs. Case Temperature



0.1
0.1
0.1
0.02
0.02
0.02
0.02
10⁻⁴
10⁻³
10⁻²
10⁻¹
1
10
30

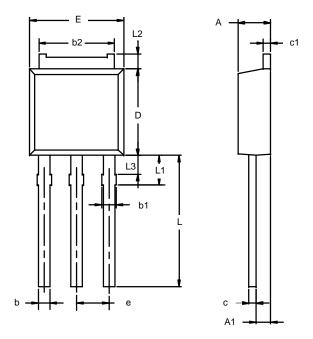
Square Wave Pulse Duration (s)
Normalized Thermal Transient Impedance, Junction-to-Case

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Normalized Effective Transient Thermal Impedance



TO-251AA



Note: Dimension L3 is for reference only.

	MILLIN	IETERS	INCHES		
Dim	Min	Max	Min	Max	
Α	2.21	2.38	0.087	0.094	
A 1	0.89	1.14	0.035	0.045	
b	0.71	0.89	0.028	0.035	
b1	0.76	1.14	0.030	0.045	
b2	5.23	5.43	0.206	0.214	
С	0.46	0.58	0.018	0.023	
с1	0.46	0.58	0.018	0.023	
D	5.97	6.22	0.235	0.245	
Е	6.48	6.73	0.255	0.265	
е	2.28 BSC		0.090	BSC	
L	3.89	9.53	0.153	0.375	
L1	1.91	2.28	0.075	0.090	
L2	0.89	1.27	0.035	0.050	
L3	1.15	1.52	0.045	0.060	

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